

FQPF12N60CT

600V N-Channel MOSFET

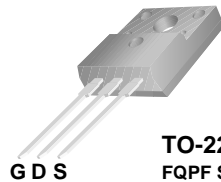
Features

- 12A, 600V, $R_{DS(on)} = 0.65\Omega @ V_{GS} = 10V$
- Low gate charge (typical 48 nC)
- Low C_{rss} (typical 21 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.



TO-220F Potted
FQPF Series



Absolute Maximum Ratings

Symbol	Parameter	FQPF12N60CT	Units
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	12*	A
	- Continuous ($T_C = 100^\circ\text{C}$)	7.4*	A
I_{DM}	Drain Current - Pulsed (Note 1)	48*	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	870	mJ
I_{AR}	Avalanche Current (Note 1)	12	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	5.1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	51	W
	- Derate above 25°C	0.41	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQPF12N60CT	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.43	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQPF12N60CT	FQPF12N60CT	TO-220F	--	--	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	600	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 480 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6 A	--	0.53	0.65	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 6 A (Note 4)	--	13	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1760	2290	pF
C _{oss}	Output Capacitance		--	182	235	pF
C _{rss}	Reverse Transfer Capacitance		--	21	28	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 12A, R _G = 25 Ω (Note 4, 5)	--	30	70	ns
t _r	Turn-On Rise Time		--	85	180	ns
t _{d(off)}	Turn-Off Delay Time		--	140	290	ns
t _f	Turn-Off Fall Time		--	90	190	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 12A, V _{GS} = 10 V (Note 4, 5)	--	48	63	nC
Q _{gs}	Gate-Source Charge		--	8.5	--	nC
Q _{gd}	Gate-Drain Charge		--	21	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 12 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 12 A, dI _F / dt = 100 A/μs (Note 4)	--	420	--	ns
Q _{rr}	Reverse Recovery Charge		--	4.9	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 11mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 12A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

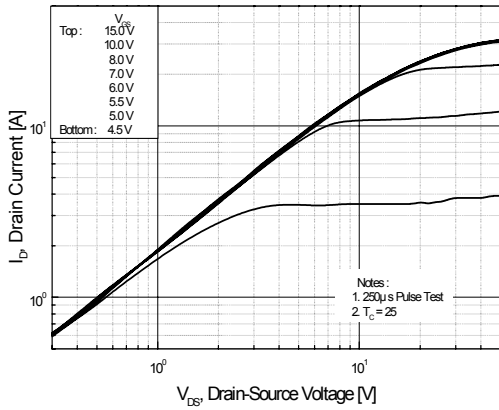


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

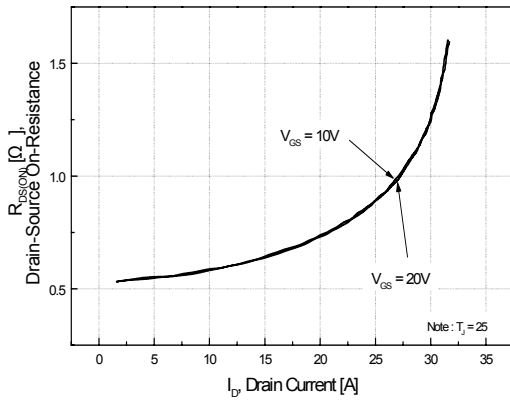


Figure 5. Capacitance Characteristics

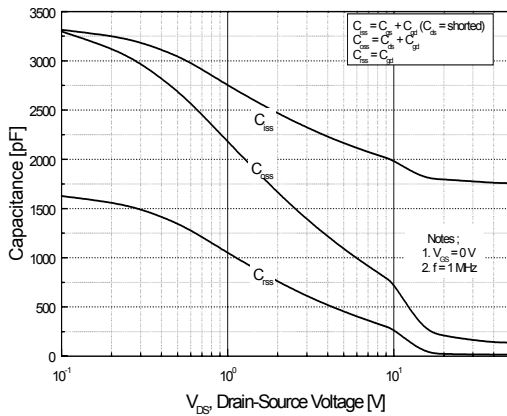


Figure 2. Transfer Characteristics

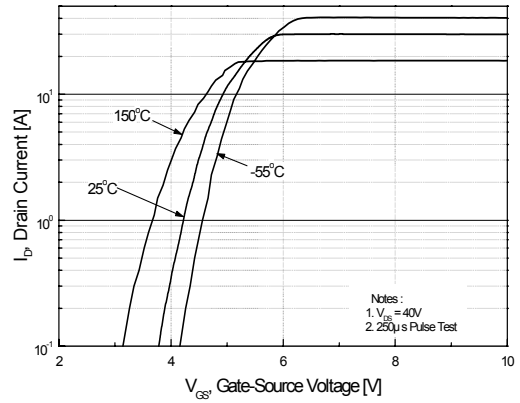


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

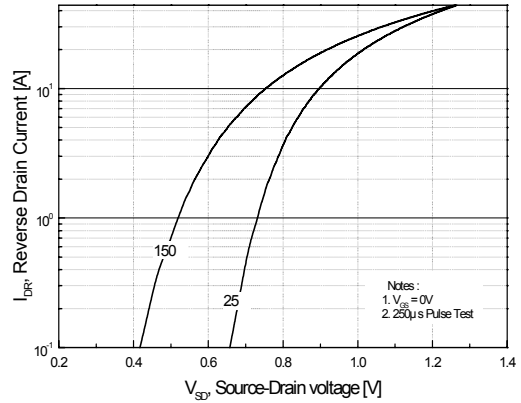
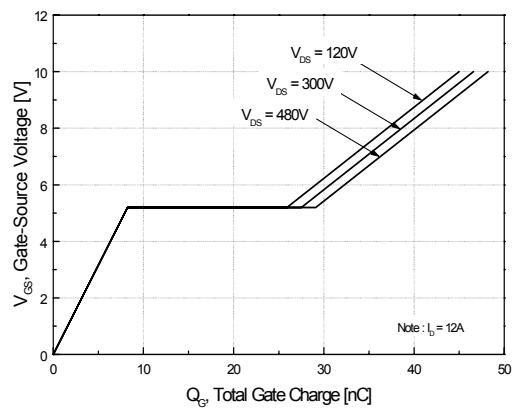


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

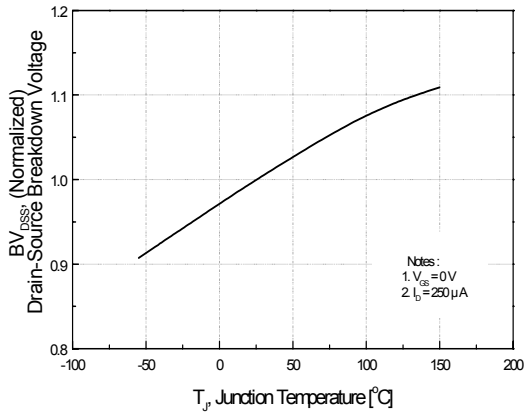


Figure 8. On-Resistance Variation vs. Temperature

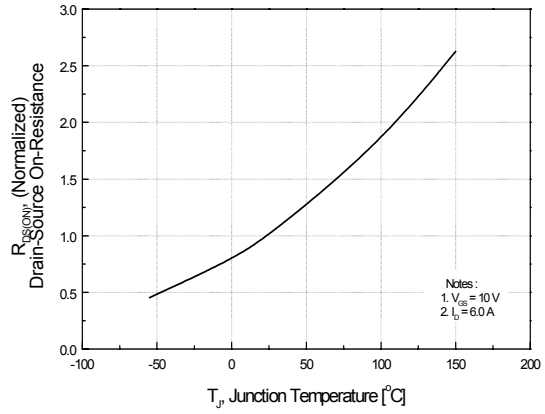


Figure 9. Maximum Safe Operating Area

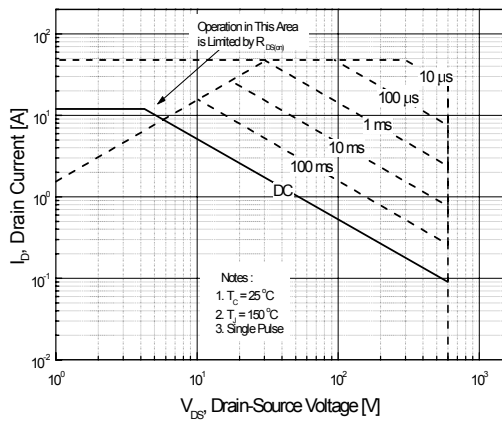


Figure 10. Maximum Drain Current vs. Case Temperature

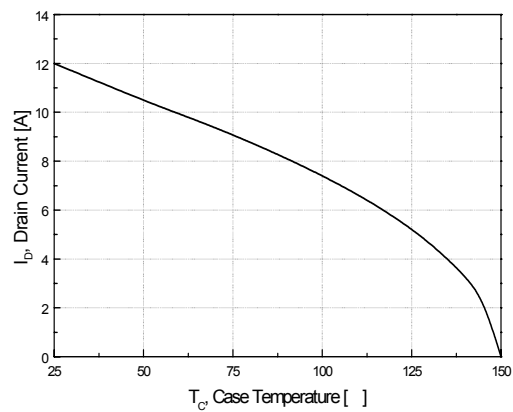
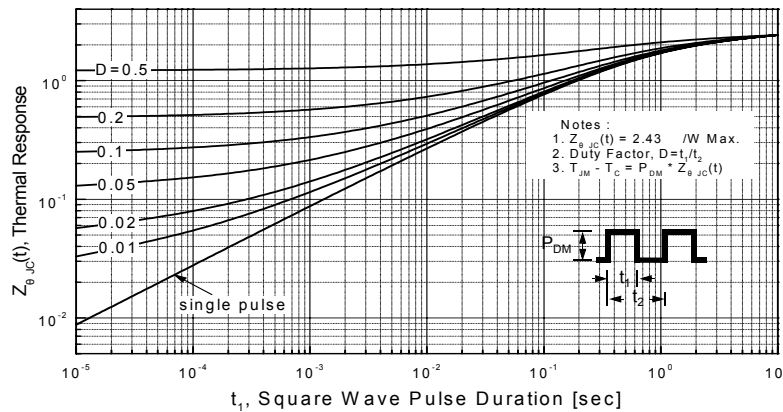


Figure 11. Transient Thermal Response Curve



Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

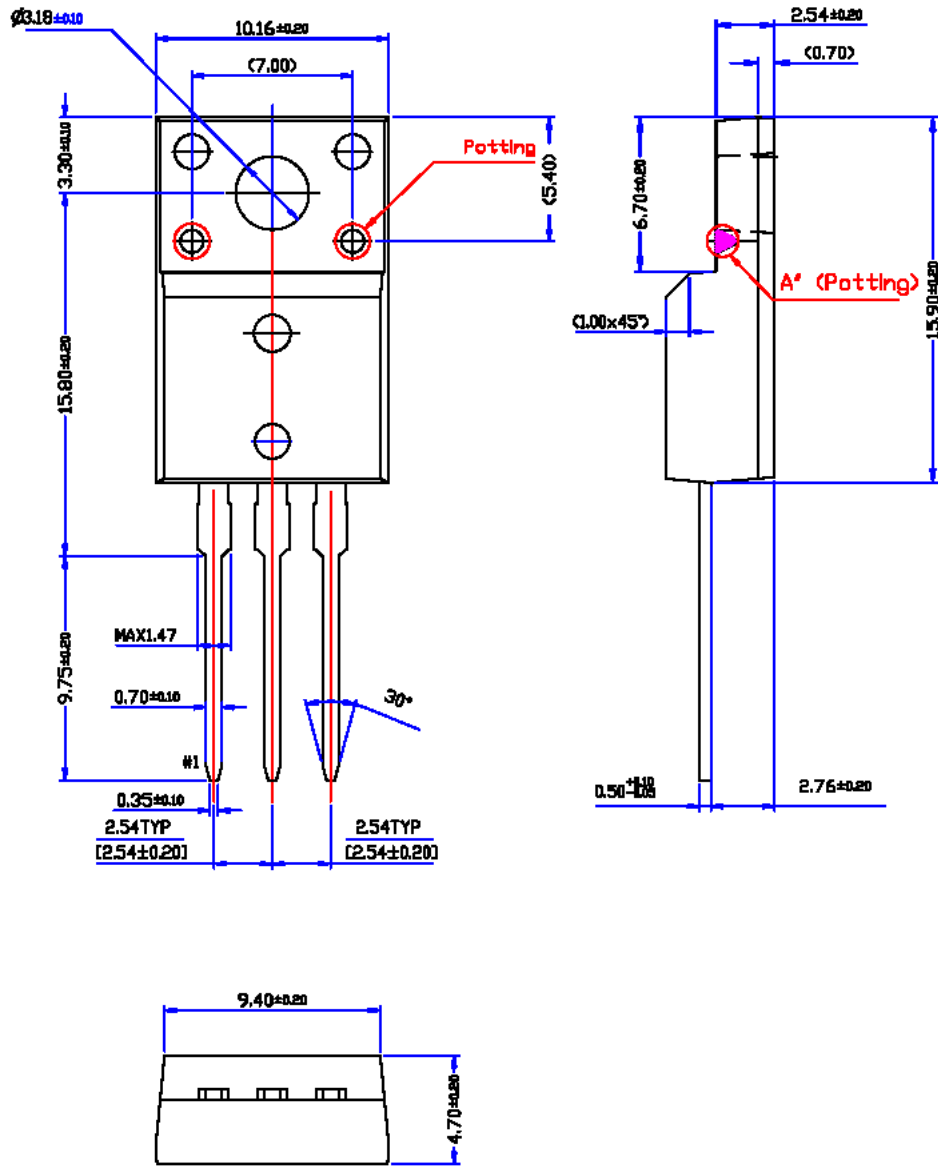


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220F Potted



* Front/Back Side Isolation Voltage : 4000V

Dimensions in Millimeters

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FASTr™	MicroPak™	QT Optoelectronics™	TinyPWM™	
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